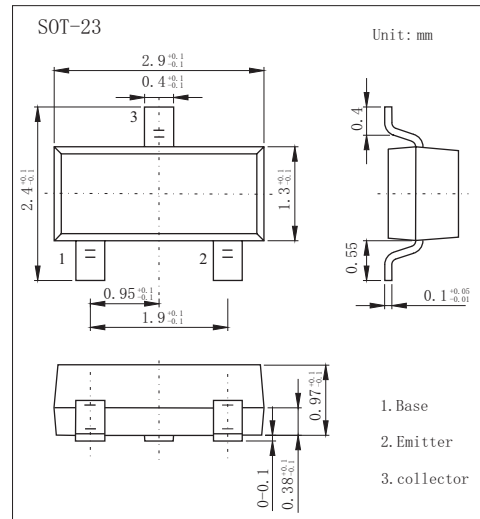


PNP Transistor

■ Features

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-80	V
Collector - Emitter Voltage	V_{CEO}	-65	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu\text{A}$, $I_E = 0$	-80			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 \text{ mA}$, $I_B = 0$	-65			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -70 \text{ V}$, $I_E = 0$			-100	nA
Collector- emitter cut-off current	I_{CEO}	$V_{CE} = -55 \text{ V}$, $I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 \text{ V}$, $I_C = 0$			-100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{ mA}$, $I_B = -5 \text{ mA}$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100 \text{ mA}$, $I_B = -5 \text{ mA}$			-1.1	
DC current gain	h_{FE}	$V_{CE} = -5 \text{ V}$, $I_C = -2 \text{ mA}$	420		800	
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}$, $f = 1 \text{ MHz}$			4.5	pF
Transition frequency	f_T	$V_{CE} = -5 \text{ V}$, $I_C = -10 \text{ mA}$, $f = 100 \text{ MHz}$	100			MHz

■ Marking

Marking 3C

PNP Transistor

■ Typical Characteristics

